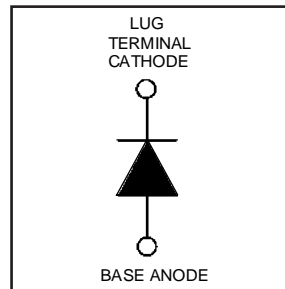


HFA105NH60R

Ultrafast, Soft Recovery Diode

Features

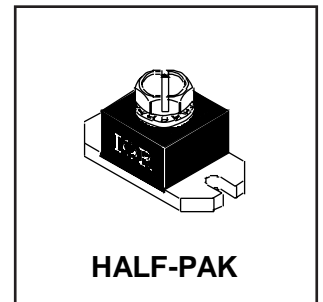
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 600V$
$V_F(\text{typ.})^{\text{③}} = 1.2V$
$I_{F(AV)} = 105A$
$Q_{rr}(\text{typ.}) = 450nC$
$I_{RRM}(\text{typ.}) = 10A$
$t_{rr}(\text{typ.}) = 35ns$
$di_{(rec)M}/dt(\text{typ.})^{\text{③}} = 240A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	600	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	147	A
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	72	
I_{FSM}	Single Pulse Forward Current ①	600	
E_{AS}	Non-Repetitive Avalanche Energy ②	220	μJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	379	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	152	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	—	—	0.33	$^\circ C/W$
R_{thCS}	Case-to-Sink, Flat, Greased Surface	—	0.15	—	K/W
Wt	Weight	—	26 (0.9)	—	g (oz)
	Mounting Torque ④	15 (1.7)	—	25 (2.8)	lbf•in
	Terminal Torque	30 (3.4)	—	40 (4.6)	(N•m)
	Vertical Pull	—	—	80	lbf•in
	2 inch Lever Pull	—	—	40	

Note: ① Limited by junction temperature
 ② $L = 100\mu H$, duty cycle limited by max T_J
 ③ $125^\circ C$

④ Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film of thermal grease to mounting surface. Gradually tighten each mounting bolt in 5-10 lbf•in steps until desired or maximum torque limits are reached. Module

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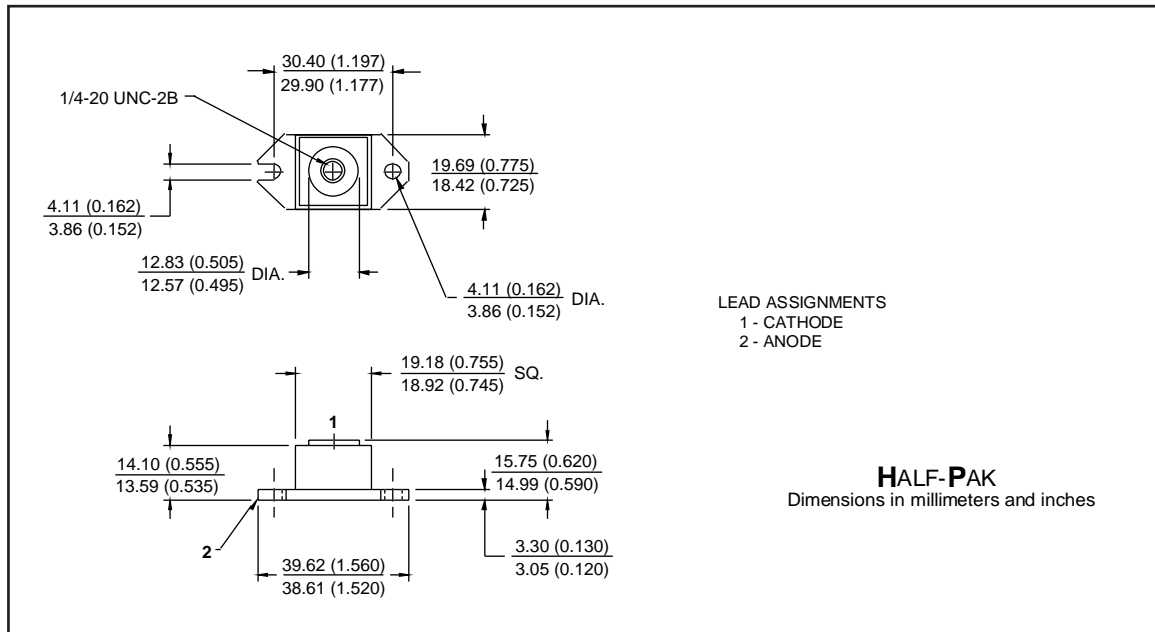
International
IOR Rectifier

Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR} Cathode Anode Breakdown Voltage	600	—	—	V	$I_R = 100\mu\text{A}$
V_{FM} Max Forward Voltage See Fig. 1	—	1.3	1.5	V	$I_F = 105\text{A}$
	—	1.5	1.7		$I_F = 210\text{A}$
	—	1.2	1.4		$I_F = 105\text{A}, T_J = 125^\circ\text{C}$
I_{RM} Max Reverse Leakage Current See Fig. 2	—	6.0	30	μA	$V_R = V_R$ Rated
	—	1.5	6.0	mA	$T_J = 125^\circ\text{C}, V_R = 480\text{V}$
C_T Junction Capacitance See Fig. 3	—	200	300	pF	$V_R = 200\text{V}$
L_S Series Inductance	—	6.0	—	nH	From top of terminal hole to mounting plane

Dynamic Recovery Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions	
t_{rr} Reverse Recovery Time See Fig. 5	—	35	—	ns	$I_F = 1.0\text{A}, di_f/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$ $T_J = 25^\circ\text{C}$	
t_{rr1}	—	90	140			$T_J = 125^\circ\text{C}$
t_{rr2}	—	160	240			
I_{RRM1} Peak Recovery Current See Fig. 6	—	10	18	A	$T_J = 25^\circ\text{C}$ $V_R = 200\text{V}$	
I_{RRM2}	—	15	30			
Q_{rr1} Reverse Recovery Charge See Fig. 7	—	450	1300	nC	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
Q_{rr2}	—	1200	3600			
$di_{(rec)M}/dt1$ Peak Rate of Fall of Recovery Current During t_b See Fig. 8	—	310	—	A/ μs	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
$di_{(rec)M}/dt2$	—	240	—			



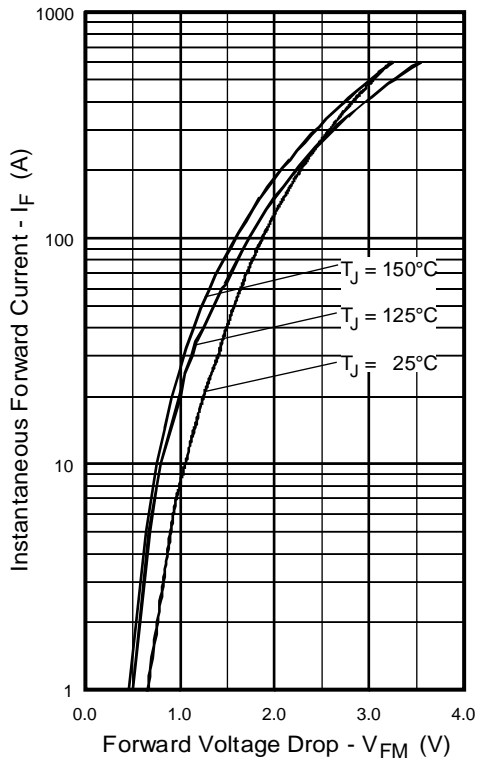


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

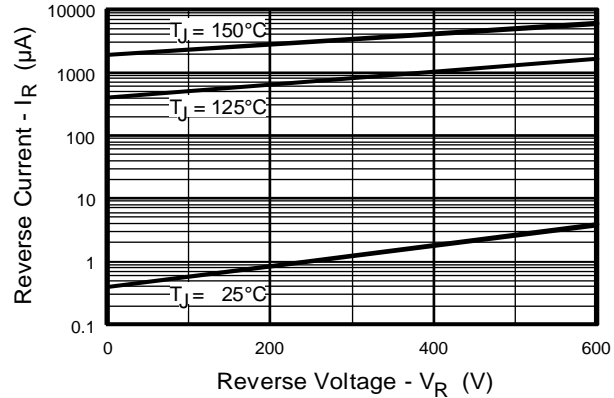


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

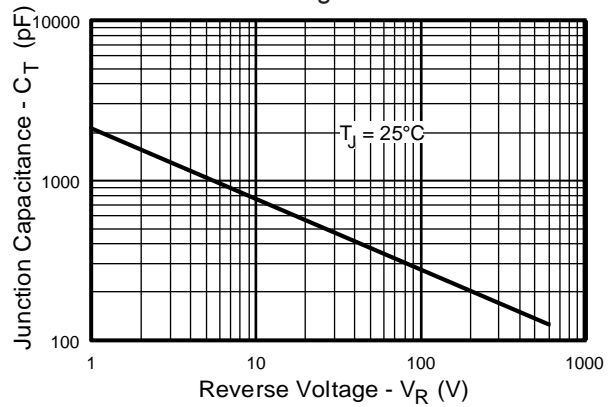


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

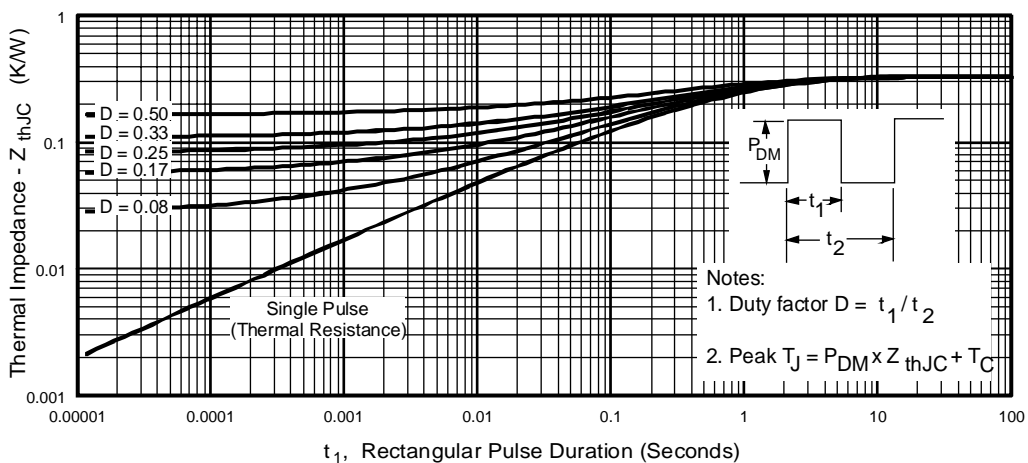


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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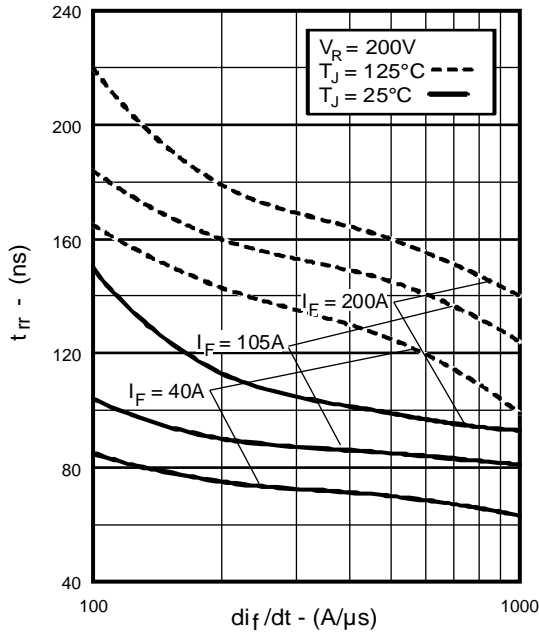


Fig. 5 - Typical Reverse Recovery vs. di_f/dt

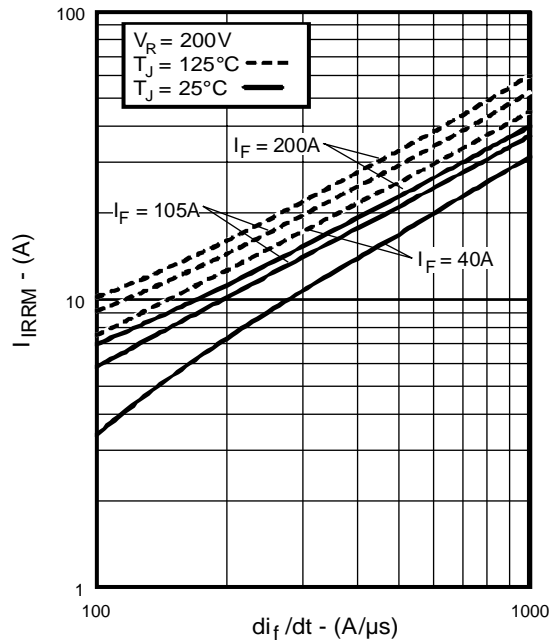


Fig. 6 - Typical Recovery Current vs. di_f/dt

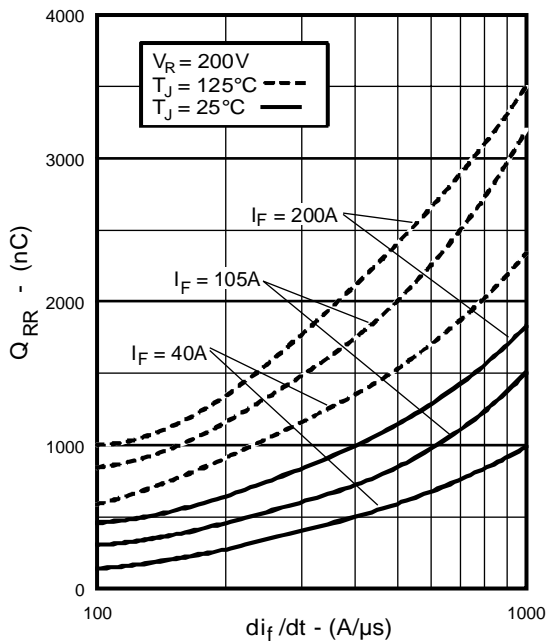


Fig. 7 - Typical Stored Charge vs. di_f/dt

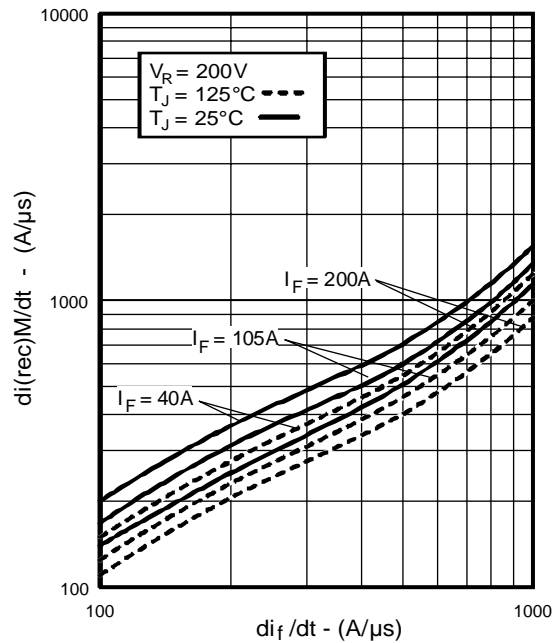


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

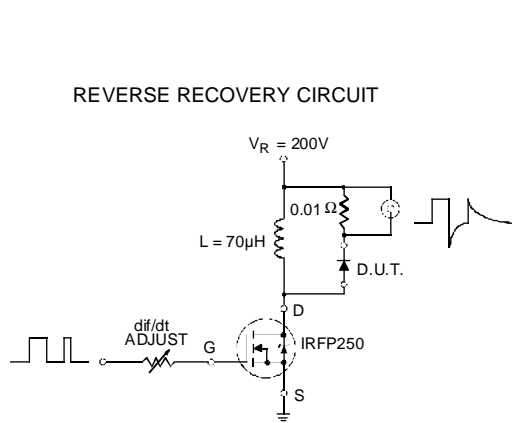


Fig. 9 - Reverse Recovery Parameter Test Circuit

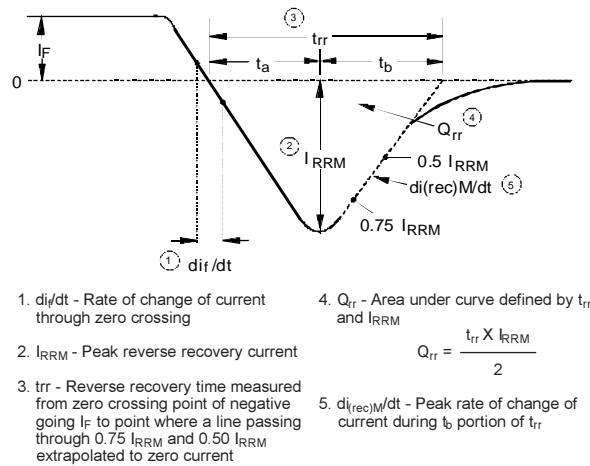


Fig. 10 - Reverse Recovery Waveform and Definitions

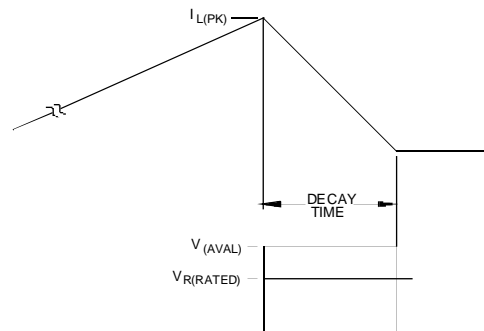
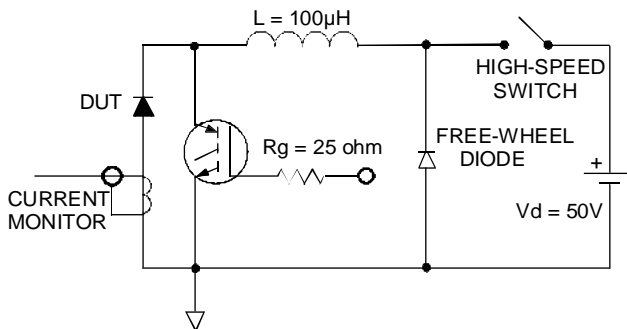


Fig. 11 - Avalanche Test Circuit and Waveforms

单击下面可查看定价，库存，交付和生命周期等信息

[>>Vishay\(威世\)](#)